

[REDACTED]

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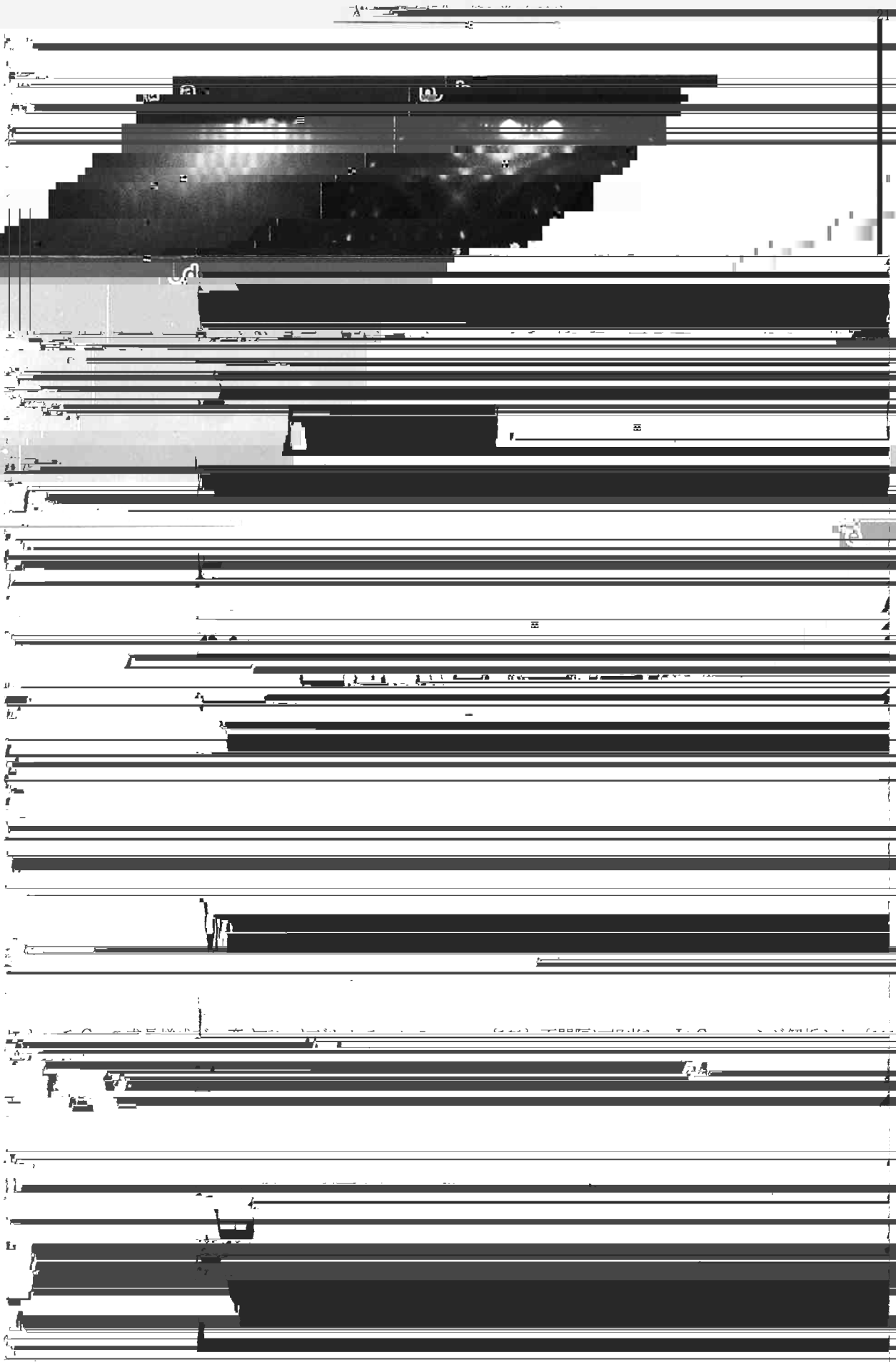
れている<sup>3)</sup>。この Surfactant という語は Surface-active

1. はじめに

[REDACTED]

[REDACTED]





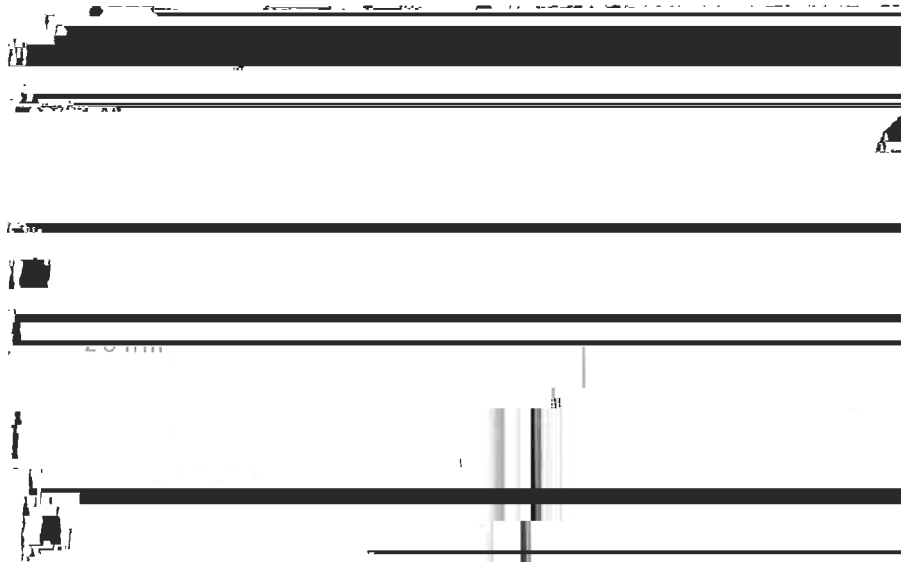
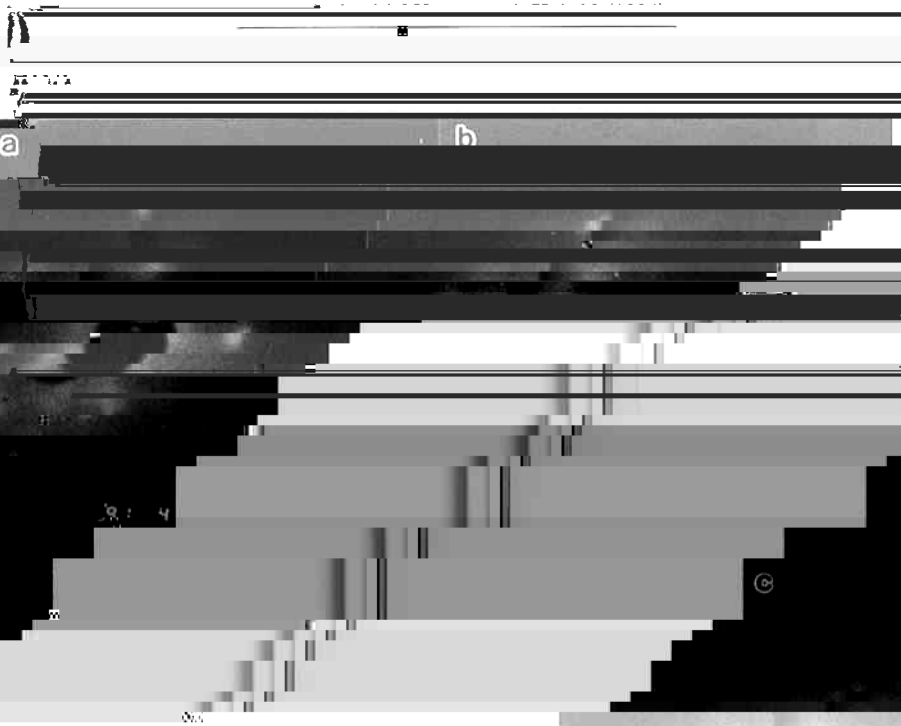
C

B

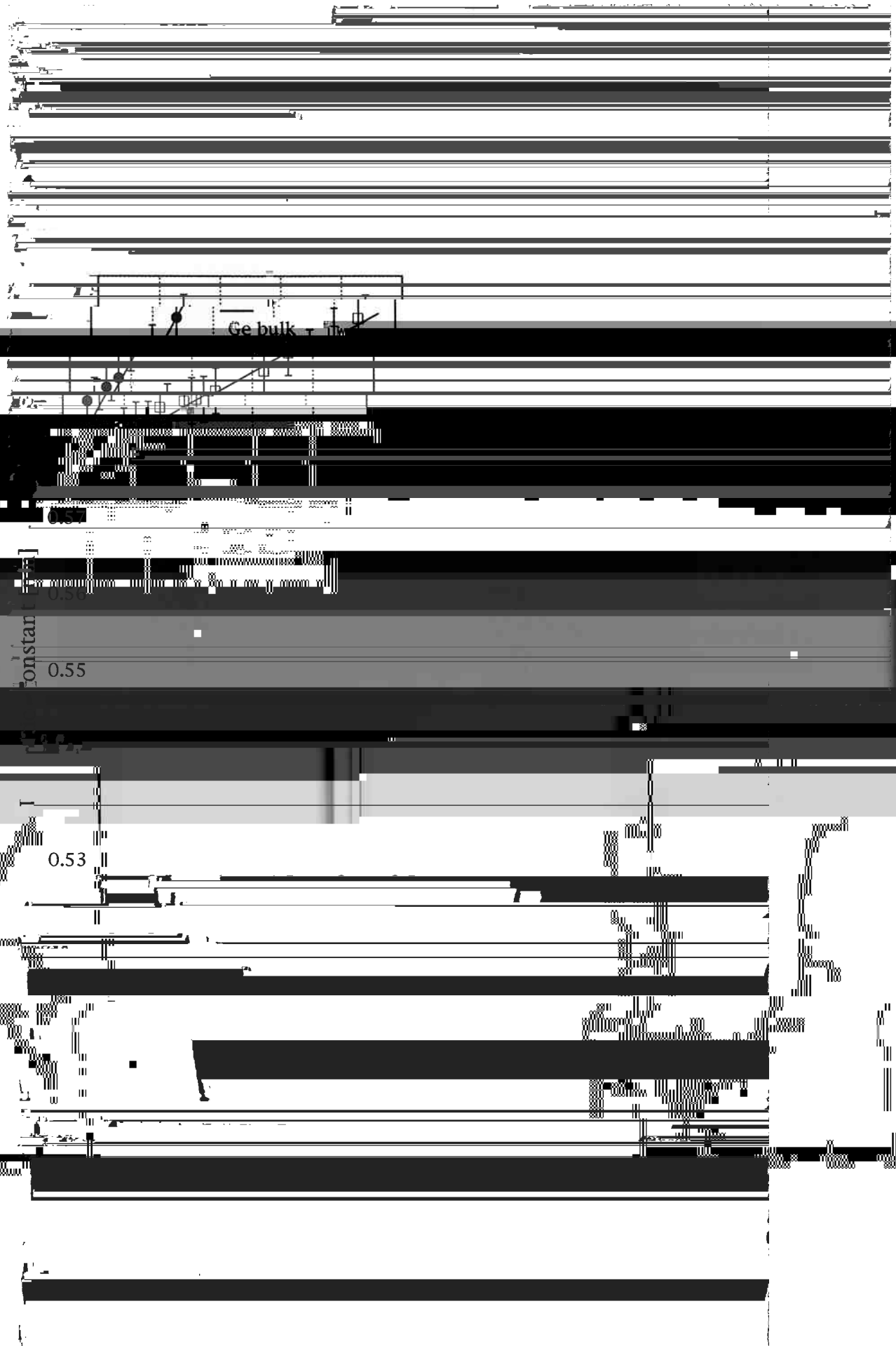
E

B

E







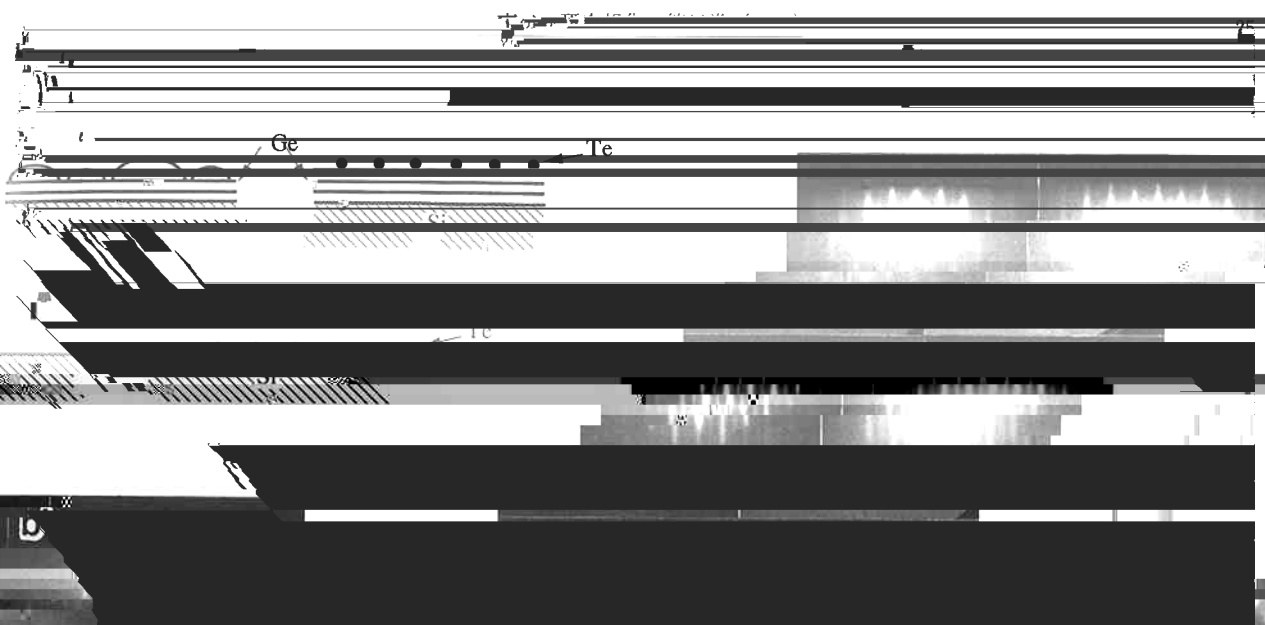


Fig. 11



Fig. 10 RHEED patterns in  $[110]$  azimuth of Ge

layer with (a) 0.0 ML, (b) 0.05 ML, (c) 0.1

ML, (d) 0.2 ML, (e) 0.6 ML, (f) 1.0 ML.

Te.

Te 0.1ML

270°C

Fig. 13 Attenuation feature of Si photoelectron in-

270°C.

0.7



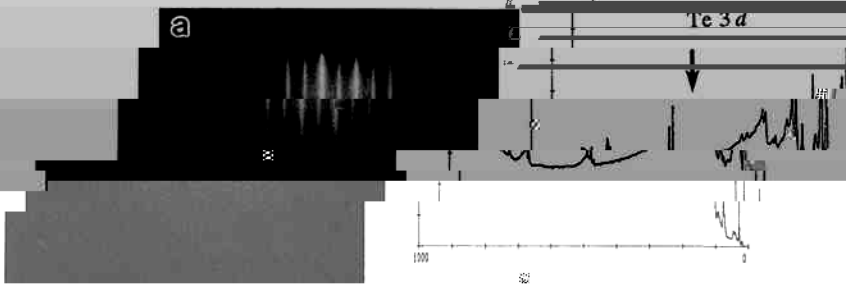
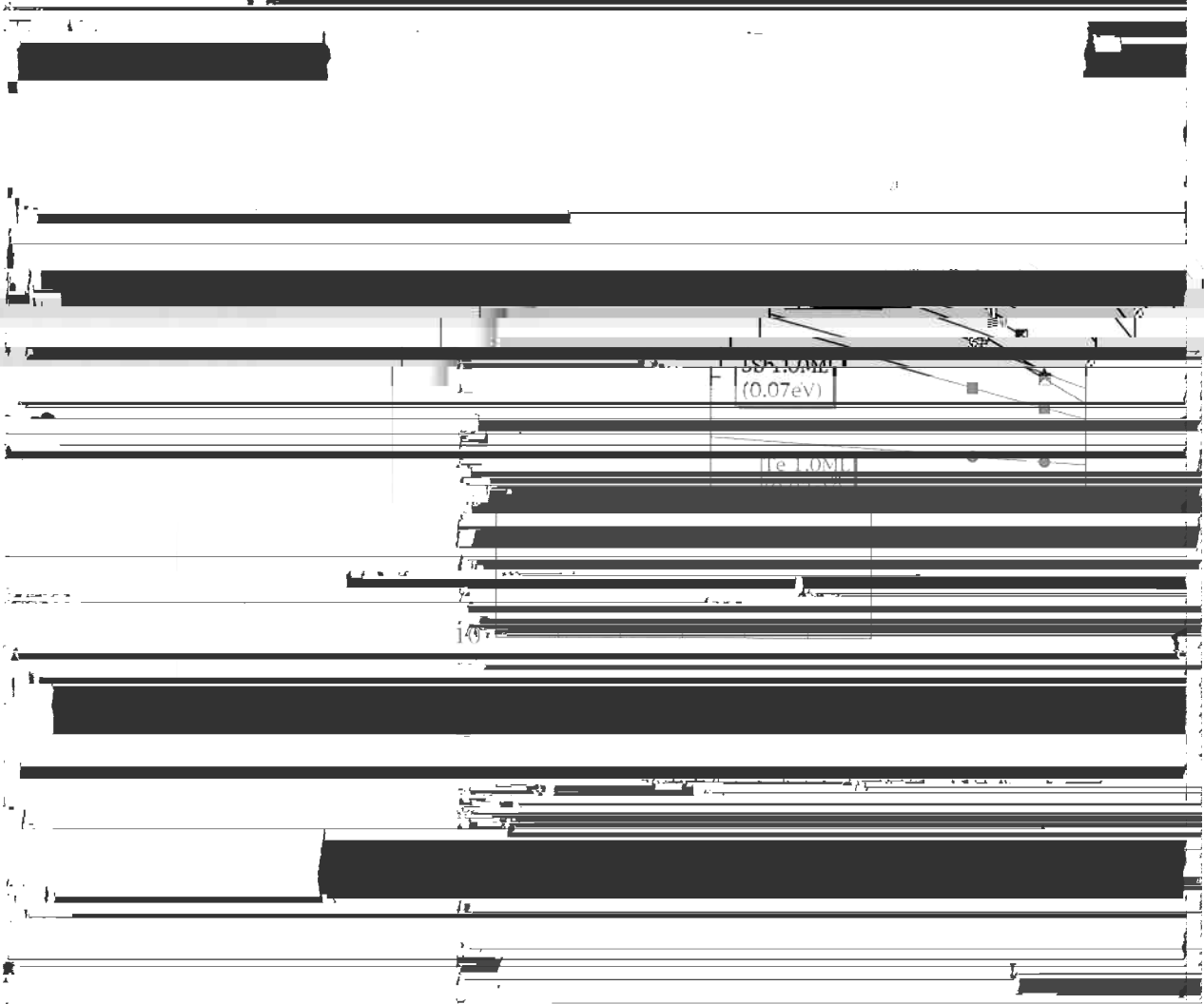


Fig. 15 (a) (b) (c) after post-annealing of 10h at 450°C



atom

0.09 eV となっており、非常に近い値になっている。こ

Te,Sb

25

Ge/Si

T<sub>c</sub>=270°C



Te

5

Te

0 0.2 0.4 0.6 0.8 1.0

Amount of surfactant (ml)

Amount of surfactant (ml)

25

(分) 12.12.12 12.12.12 12.12.12 12.12.12 12.12.12

[REDACTED]

[REDACTED]

参考文献

[REDACTED]

参考文献

V. N. ... 1991

L465 (1991)

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昭和59年9月15日

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電研室

主任研究員

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